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Kind regards,

Team Nexperia



PMBT3906YS

40 V, 200 mA PNP/PNP general-purpose double transistor Rev. 02 — 13 May 2009 Product data s

Product data sheet

1. Product profile

1.1 General description

PNP/PNP general-purpose double transistor in a SOT363 (SC-88) very small Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		_		Package	
	NXP	JEITA	complement	complement	configuration	
PMBT3906YS	SOT363	SC-88	PMBT3904YS	PMBT3946YPN	very small	

1.2 Features

- General-purpose double transistor
- Board-space reduction
- AEC-Q101 qualified

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-200	mA
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V};$ $I_{C} = -10 \text{ mA}$	100	180	300	



Pinning information 2.

Pinning Table 3

Table 5.	i iiiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1	D. D. D.	
2	base TR1	6 5 4	6 5 4
3	collector TR2		TR2
4	emitter TR2	0	(TR1)
5	base TR2	□1 □2 □3	
6	collector TR1		1 2 3
			sym018

Ordering information 3.

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PMBT3906YS	SC-88	plastic surface-mounted package; 6 leads	SOT363

Marking 4.

Product data sheet

Table 5. **Marking codes**

Type number	Marking code ^[1]
PMBT3906YS	BD*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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-65

+150

٥С

5. Limiting values

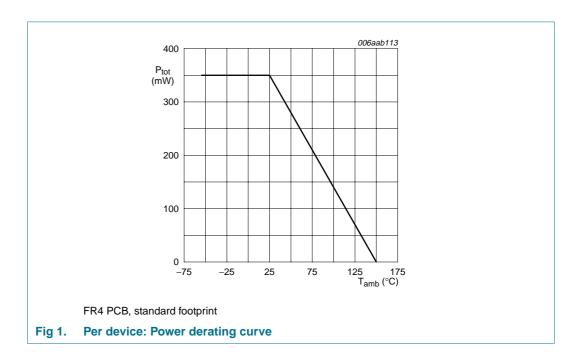
Table 6. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

storage temperature

 T_{stg}

Symbol	Parameter	Conditions	Min	Max	Unit
Per transisto	or				
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-200	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	230	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	350	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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Product data sheet

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40 V, 200 mA PNP/PNP general-purpose double transistor

Thermal characteristics 6.

Table 7. Thermal characteristics

145.5 11	or mar or ar a otto rotroo					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	543	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	290	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	357	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

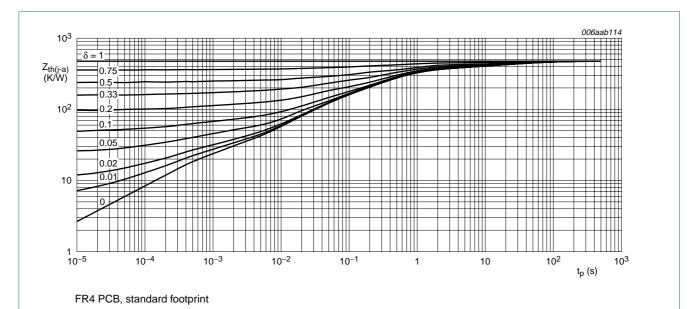


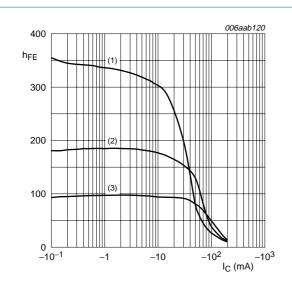
Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-50	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 \text{ V}; I_C = 0 \text{ A}$	-	-	–50	nA
h _{FE}	DC current gain	$V_{CE} = -1 V$				
		$I_{C} = -0.1 \text{ mA}$	60	180	-	
		$I_C = -1 \text{ mA}$	80	180	-	
		$I_C = -10 \text{ mA}$	100	180	300	
		$I_C = -50 \text{ mA}$	60	130	-	
		$I_C = -100 \text{ mA}$	30	50	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -1 \text{ mA}$	-	-100	-250	mV
		$I_C = -50 \text{ mA};$ $I_B = -5 \text{ mA}$	-	-165	-400	mV
22001	base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -1 \text{ mA}$	-	-750	-850	mV
		$I_C = -50 \text{ mA};$ $I_B = -5 \text{ mA}$	-	-850	-950	mV
f _T	transition frequency	$V_{CE} = -20 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	250	-	-	MHz
C _c	collector capacitance	$V_{CB} = -5 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	4.5	pF
C _e	emitter capacitance	$V_{BE} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	10	pF
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A};$ $R_{S} = 1 k\Omega;$ $f = 10 \text{ Hz to } 15.7 \text{ kHz}$	-	-	4	dB
t _d	delay time	$V_{CC} = -3 \text{ V};$	-	-	35	ns
t _r	rise time	$I_{C} = -10 \text{ mA};$ $I_{Bon} = -1 \text{ mA};$ $I_{Boff} = 1 \text{ mA}$	-	-	35	ns
t _{on}	turn-on time		-	-	70	ns
t _s	storage time		-	-	225	ns
t _f	fall time		-	-	75	ns
t _{off}	turn-off time		-	-	300	ns



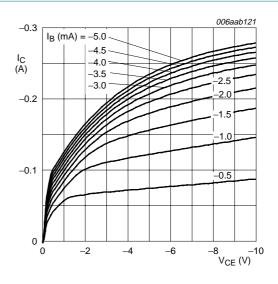
 $V_{CE} = -1 V$

(1) $T_{amb} = 150 \, ^{\circ}C$

(2) $T_{amb} = 25 \,^{\circ}C$

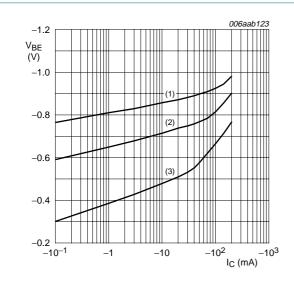
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Collector current as a function of Fig 4. collector-emitter voltage; typical values



 $V_{CE} = -1 V$

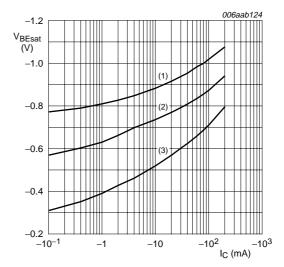
(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Product data sheet

Base-emitter voltage as a function of collector Fig 5. current; typical values



 $I_{\rm C}/I_{\rm B}=10$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 150 \, ^{\circ}C$

Base-emitter saturation voltage as a function Fig 6. of collector current; typical values

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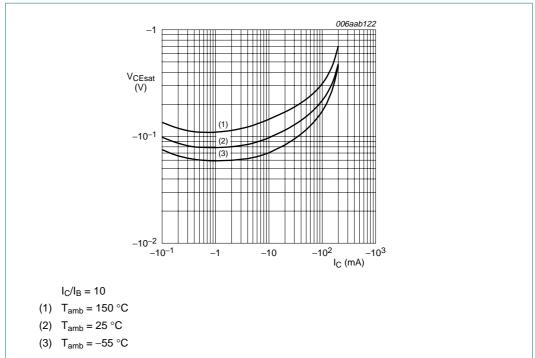
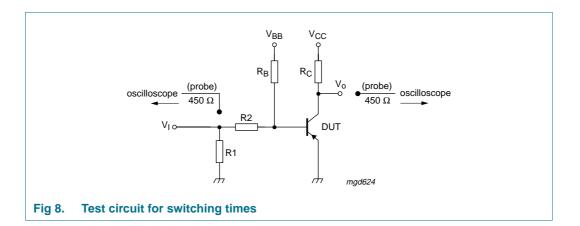


Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

8. Test information

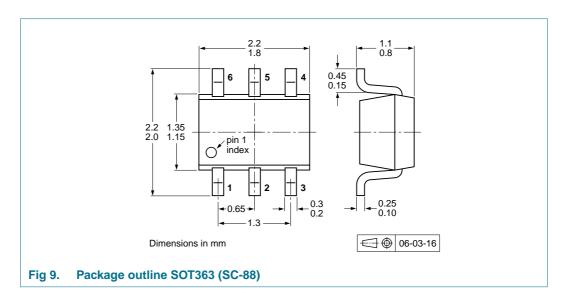


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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Package outline



10. Packing information

Product data sheet

Table 9. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity	
				3000	10000
PMBT3906YS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

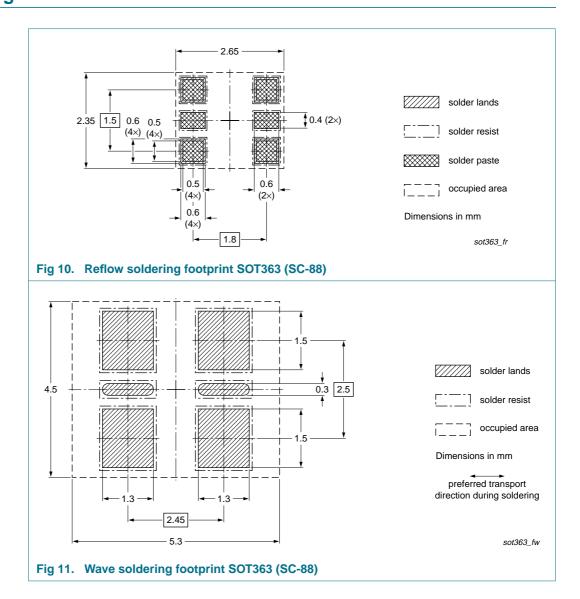
[3] T2: reverse taping

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PMBT3906YS

40 V, 200 mA PNP/PNP general-purpose double transistor

11. Soldering





12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3906YS_2	20090513	Product data sheet	-	PMBT3906YS_1
Modifications:	• Figure 4: am	nended		
PMBT3906YS_1	20080306	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PMBT3906YS

40 V, 200 mA PNP/PNP general-purpose double transistor

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